#### 查询MAX4524供应商

19-1332; Rev 0; 1/98



## Low-Voltage, Single-Supply Multiplexer and Switch

### **General Description**

The MAX4524/MAX4525 are low-voltage, single-supply CMOS analog switches configured as a 4-channel multiplexer/demultiplexer (MAX4524) and a doublepole/double-throw (DPDT) switch (MAX4525). Both have an inhibit input to simultaneously open all signal paths.

These devices operate from a single supply of +2V to +12V and are optimized for operation with +3V or +5V supplies. On-resistance is  $200\Omega$  with a +5V supply and  $500\Omega$  with a +3V supply. Each switch can handle Rail-to-Rail<sup>®</sup> analog signals. The off-leakage current is only 2nA at +25°C or 20nA at +85°C.

All digital inputs have 0.8V to 2.4V logic thresholds, ensuring TTL/CMOS-logic compatibility when using a single +5V supply.

#### **Applications**

Battery-Operated Equipment Audio and Video Signal Routing Low-Voltage Data-Acquisition Systems Communications Circuits

#### Features

- Tiny 10-Pin µMAX Package
- Single-Supply Operation from +2V to +12V
- 200Ω On-Resistance with +5V Supply
- **500**Ω On-Resistance with +3V Supply
- + Guaranteed 8Ω On-Resistance Match at +5V
- Guaranteed 2nA Max On-Leakage at +5V
- TTL/CMOS-Logic Compatible

#### \_Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
MAX4524CUB	0°C to +70°C	10 µMAX
MAX4524C/D	0°C to +70°C	Dice*
MAX4524EUB	-40°C to +85°C	10 µMAX
MAX4525CUB	0°C to +70°C	10 µMAX
MAX4525C/D	0°C to +70°C	Dice*
MAX4525EUB	-40°C to +85°C	10 µMAX

\* Contact factory for availability.

#### TOP VIEW MAXIM MAXIM MAX4524 MAX4525 NO2 10 V+ 10 V+ NOA NO3 9 COM COMA 9 COMB 8 NO0 8 NOB NO1 NCA 7 7 ADDA INH LOGIC INH NCB GND 5 ADDB 6 6 GND LOGIC ADD μΜΑΧ μΜΑΧ INH ADDB ADDA ON SWITCH INH ADD ON SWITCH NONE 1 NONE Х X 1 Х 0 0 0 COM-NO0 COMA-NCA 0 0 COMB-NCB 0 0 1 COM-NO1 COMA-NOA 0 1 0 1 0 COM-NO2 COMB-NOB 0 COM-NO3 1 1 X = DON'T CARE Rail-to-Rail is a registered trademark of Nippon Motorola Ltd.

Pin Configurations/Functional Diagrams/Truth Tables

MAX4524/MAX4525

Maxim Integrated Products 1

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### **ABSOLUTE MAXIMUM RATINGS**

(Voltages Referenced to GND)

V+		0.3V, +13V
Voltage into ar	ny terminal (Note 1)	0.3V to (V+ + 0.3V)
Continuous Cu	urrent into any Terminal	±20mA
Peak Current,	NO, NC or COM_	
(pulsed at 1)	ms,10% duty cycle)	±40mA
	od 3015.7	

Continuous Power Dissipation ( $T_A = +70^{\circ}C$ ) $\mu$ MAX (derate 4.1mW/°C above +70°C)	330mW
Operating Temperature Ranges	
MAX452_C	0°C to +70°C
MAX452_E	40°C to +85°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10sec)	+300°C

**Note 1:** Voltages exceeding V+ or GND on any signal terminal are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### ELECTRICAL CHARACTERISTICS—Single +5V Supply

(V+ = +4.5V to +5.5V, GND = 0V, V<sub>AH</sub> = 2.4V, V<sub>AL</sub> = 0.8V, T<sub>A</sub> = T<sub>MIN</sub> to T<sub>MAX</sub>, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	TEMP.	MIN	TYP (Note 2)	MAX	UNITS		
ANALOG SWITCH	1			1				1	
Analog Signal Range	Vcom, V <sub>NO</sub>			C, E	V-		V+	V	
COM-NO/NC On-Resistance	Ron	V+ = 4.5V, ICOM = 1mA, VCOM	2 51/	+25°C		90	150		
COM-NO/NC ON-Resistance	RON	v + = 4.5v, ICOM = IIIA, VCOM	= 3.5V	C, E			200 Ω		
COM-NO/NC On-Resistance Match Between Channels	ΔR <sub>ON</sub>	V+ = 4.5V, I <sub>COM</sub> = 1mA, V <sub>COM</sub>	V+ = 4.5V, I <sub>COM</sub> = 1mA, V <sub>COM</sub> = 3.5V			2	10	Ω	
(Note 3)				C, E			15		
COM-NO/NC On-Resistance Flatness (Note 4)	R <sub>FLAT</sub>	V+ = 5.5V; I <sub>COM</sub> = 1mA; V <sub>COM</sub> = 1.5V, 2.5V, 3.5V		+25°C		5	12	Ω	
NO/NC Off-Leakage	INO(OFF),	$V_{+} = 5.5V; V_{NO} = 1V, 4.5V; V_{CO}$	4 5 / 1 /	+25°C	-1		1	nA	
(Note 5)	INC(OFF),	$v + = 5.5v; v_{NO} = 1v, 4.5v; v_{CC}$	)M = 4.3V, IV	C, E -10		10	- 11A		
	ICOM(OFF)	V+ = 5.5V; V <sub>NO</sub> = 1V, 4.5V; V <sub>COM</sub> = 4.5V, 1V	MAX4524	+25°C	-2		2	nA nA	
COM Off-Leakage				C, E	-50		50		
(Note 5)			MAX4525	+25°C	-1		1		
			101474525	C, E	-25		25		
		M(ON) V+ = 5.5V; V <sub>COM</sub> = 4.5V, 1V	MAX4524	+25°C	-2		2		
COM On-Leakage			101/1/14024	C, E	-50		50		
(Note 5)			MAX4525	+25°C	-1		1		
			WIAX4525		-25		25		
DIGITAL I/O									
Logic Input Logic Threshold High	VIH			C, E		1.5	2.4	V	
Logic Input Logic Threshold Low	VIL			C, E	0.8	1.5		V	
Input Current High	IIН	$V_A = V_{INH} = 2.4V$		C, E	-1		1	μA	
Input Current Low	IIН	$V_A = V_{INH} = 0.8V$		C, E	-1		1	μA	

### ELECTRICAL CHARACTERISTICS—Single +5V Supply (continued)

 $(V_{+} = +4.5V \text{ to } +5.5V, \text{ GND} = 0V, V_{AH} = 2.4V, V_{AL} = 0.8V, T_{A} = T_{MIN} \text{ to } T_{MAX}$ , unless otherwise noted. Typical values are at  $T_{A} = +25^{\circ}\text{C.}$ 

PARAMETER	SYMBOL	CONDITIONS		TEMP.	MIN	TYP (Note 2)	MAX	UNITS
SWITCH DYNAMIC CHARA	CTERISTIC	6		1				
Inhibit Turn-On Time	t(ON)	$V_{\rm NO_{-}} = 3V, R_{\rm L} = 300\Omega, C_{\rm L} = 35$	pF,	+25°C		90	150	ns
	(011)	Figure 2		C, E			200	-
Inhibit Turn-Off Time	t(OFF)	$V_{NO} = 3V, R_L = 300\Omega, C_L = 35$	pF,	+25°C		40	120	ns
	( · · /	Figure 2		C, E			180	
Address Transition Time	<b>t</b> TRANS	$V_{NO} = 3V/0V, R_L = 300\Omega, C_L =$	35pF,	+25°C		90	150	ns
		Figure 1		C, E			200	
Break-Before-Make Time	<b>t</b> BBM	$V_{NO_{-}} = 3V, R_{L} = 300\Omega, C_{L} = 35$	pF, Figure 3	+25°C	5	20		ns
Charge Injection (Note 6)	Q	$C=1nF,R_S=0\Omega,V_S=2.5V,F$	igure 4	+25°C		0.8	5	рС
NO/NC Off-Capacitance	CNO(OFF)	$V_{NO_{-}} = 0V, f = 1MHz, Figure 6$		+25°C		4		рF
	Coordinates	VNO = 0V f = 1MHz Figure 6	MAX4524	+25°C		14		pF
COM Off-Capacitance	CCOM(OFF)		MAX4525	+25°C		6		
COM On-Capacitance	Coontron	$V_{NO} = 0V$ , f = 1MHz, Figure 6	MAX4524	+25°C		20		- pF
COM ON-Capacitance	CCOM(ON)	$V_{NO} = 0V, T = TWHZ, TIGULE 0$	MAX4525	+25°C		12		pi
Off-Isolation	VISO	$R_L = 50\Omega$ , f = 1MHz, Figure 5		+25°C		-75		dB
Channel-to-Channel Crosstalk (MAX4525)	V <sub>CT</sub>	$R_L = 50\Omega$ , f = 1MHz, Figure 5		+25°C		-74		dB
Total Harmonic Distortion	THD	$R_L = 600\Omega$ , $V_{COM} = 2.5Vp-p$ , 20Hz to 20kHz		+25°C		0.2		%
POWER SUPPLY	•							
Power-Supply Range	V+			C, E	2		12	V
Power-Supply Current	I+	V+ = 5.5V, VADD = VINH = V+ 0	r OV	+25°C C, E	-1 -10		1 10	μA

### **ELECTRICAL CHARACTERISTICS—Single +3V Supply**

(V+ = +2.7V to +3.6V, GND = 0V, VAH = 2.0V, VAL = 0.5V, TA = T<sub>MIN</sub> to T<sub>MAX</sub>, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	TEMP.	MIN	TYP (Note 2)	MAX	UNITS	
ANALOG SWITCH								
Analog Signal Range	V <sub>COM</sub> , V <sub>NO</sub>			C, E	V-		V+	V
COM-NO/NC On-Resistance	Devi	V+ = 2.7V, ICOM = 0.1mA, VCOM = 1.5V		+25°C		190	400	Ω
	RON	Ron $V_{+} = 2.7V, I_{COM} = 0.1mA, V_{COM} = 1.5V$	1 = 1.5V	C, E			500	52
NO/NC Off-Leakage	INO(OFF),		V+ = 3.6V; V <sub>NO</sub> = 1V, 3V; V <sub>COM</sub> = 3V, 1V		-1		1	nA
(Note 6)	INC(OFF)	$v + = 3.0v, v_{\rm NO} = 1v, 3v, v_{\rm COM}$	= 30, 10	C, E	-10		10	ΠA
COM Off-Leakage (Note 6)			MAX4524	+25°C	-2		2	
		V+ = 3.6V; V <sub>NO</sub> = 1V, 3V;	101474324	C, E	-50		50	nA
	COM(OFF)	VCOM = 3V, IV	+25°C	-1		1	ПA	
			MAX4525	C, E	-25		25	



### ELECTRICAL CHARACTERISTICS—Single +3V Supply (continued)

(V+ = +2.7V to +3.6V, GND = 0V, V<sub>AH</sub> = 2.0V, V<sub>AL</sub> = 0.5V, T<sub>A</sub> = T<sub>MIN</sub> to T<sub>MAX</sub>, unless otherwise noted. Typical values are at T<sub>A</sub> = +25°C.)

PARAMETER	SYMBOL	CONDITIONS		TEMP.	MIN	TYP (Note 2)	MAX	UNITS
			MAX4524	+25°C	-2		2	
COM On-Leakage	ICOM(ON)		101AX4324	C, E	-50		50	nA
(Note 6)		v + = 3.0v, v COM = 3v, 1v	MAX4525	+25°C	-1		1	
			101474323	C, E	-25		25	
DIGITAL I/O	_							
Logic Input Logic Threshold High	VIH			C, E		1.0	2.0	V
Logic Input Logic Threshold Low	VIL			C, E	0.5	1.0		V
Input Current High	ЦН	$V_A = V_{INH} = 2.0V$		C, E	-1		1	μA
Input Current Low	Ін	$V_A = V_{INH} = 0.5V$		C, E	-1		1	μA
SWITCH DYNAMIC CHARA	CTERISTIC	<b>S</b> (Note 6)						
Inhibit Turn-On Time	t(ON)	$V_{NO_{-}}$ = 1.5V, R <sub>L</sub> = 300 $\Omega$ , C <sub>L</sub> = 35pF, Figure 2		+25°C		170	300	- ns
Initial Turn-On Time	(ON)			C, E			400	
Inhibit Turn-Off Time	t(OFF) VNO_	$V_{NO_{-}} = 1.5V$ , $R_{L} = 300\Omega$ , $C_{L} =$	$NO_{1} = 1.5V, R_{L} = 300\Omega, C_{L} = 35pF,$			50	200	ns
	(OFF)	Figure 2		C, E			300	115
Address Transition Time	me t <sub>TRANS</sub>	$V_{NO_{-}} = 1.5V/0V$ , $R_L = 300\Omega$ , $C_L = 35pF$ , Figure 1		+25°C		130	300	ns
	TRANS			C, E			400	115
Break-Before-Make Time	t <sub>BBM</sub>	Figure 3, $V_{NO_{-}}$ = 1.5V, $R_L$ = 300 $\Omega$ , $C_L$ = 35pF		+25°C	5	40		ns
POWER SUPPLY								
Power-Supply Current	+	V+ = 3.6V, V <sub>ADD</sub> = V <sub>INH</sub> = V+	$h = V_{h} = V_{\pm} \text{ or } 0 V_{\pm}$		-1		1	
Power-Supply Current		$V_{+} = 3.0V, VADD = VINH = V+$		C, E	-10		10	μΑ

Note 2: The algebraic convention is used in this data sheet; the most negative value is shown in the minimum column.

**Note 3:**  $\Delta Ron = Ron(Max) - Ron(Min)$ 

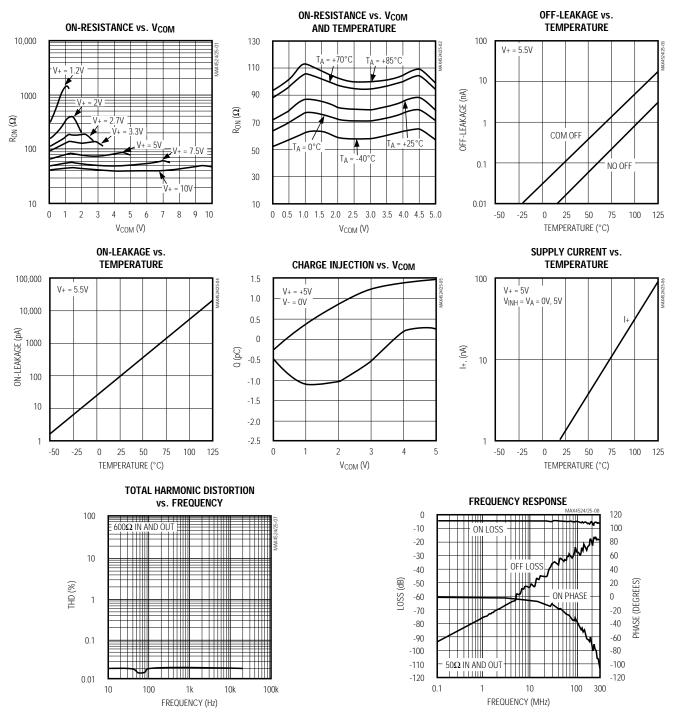
**Note 4:** Flatness is defined as the difference between the maximum and minimum value of on-resistance as measured over the specified analog signal ranges; i.e., V<sub>NO</sub> = 3V to 0V and 0V to 3V.

**Note 5:** Leakage parameters are 100% tested at maximum-rated hot operating temperature, and guaranteed by correlation at  $T_A = +25^{\circ}C$ .

Note 6: Guaranteed by design, not production tested.

(V+ = +5V, GND = 0V,  $T_A$  = +25°C, unless otherwise noted.)

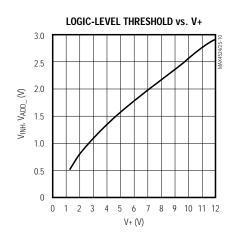
**Typical Operating Characteristics** 



MAX4524/MAX4525

M/IXI/M

 $(V + = +5V, GND = 0V, T_A = +25^{\circ}C, unless otherwise noted.)$ V+ CURRENT vs. LOGIC LEVEL 1 10-1 10-2 V + = +12V10-3 10-4 I+ CURRENT 10-5 10-6 V + = +5V10-7 10-8 10-9 10-10 10-11 0 1 2 3 4 5 6 7 8 9 10 11 12 V<sub>ADD\_</sub>, V<sub>INH</sub> (V)



**Typical Operating Characteristics (continued)** 

#### Pin Description

MAX4524	MAX4525	NAME	FUNCTION
1	_	NO2	Analog Switch Normally Open Input 2
	1	NOA	Analog Switch "A" Normally Open Input
2	—	NO3	Analog Switch Normally Open Input 3
	2	COMA	Analog Switch "A" Common
3	_	NO1	Analog Switch Normally Open Input 1
	3	NCA	Analog Switch "A" Normally Closed Input
4	4	INH	Inhibit. Connect to GND for normal operation. Connect to logic-level high to turn all switches off.
5	5	GND	Ground. Connect to digital ground (analog signals have no ground reference, but are limited to V+ and GND).
6	_	ADDB	Logic-Level Address Input (see Truth Tables)
_	6	ADD	Logic-Level Address Input (see Truth Tables)
7	_	ADDA	Logic-Level Address Input (see Truth Tables)
_	7	NCB	Analog Switch "B" Normally Closed Input
8	_	NO0	Analog Switch Normally Open Input 0
_	8	NOB	Analog Switch "B" Normally Open Input
9	_	COM	Analog Switch Common
_	9	COMB	Analog Switch "A" Common
10	10	V+	Positive Analog and Digital Supply-Voltage Input

**Note:** NO\_, NC\_, and COM\_ analog signal pins are identical and interchangeable. Any may be considered an input or output; signals pass equally well in both directions.

### **Applications Information**

#### **Power-Supply Considerations**

The MAX4524/MAX4525's construction is typical of most CMOS analog switches. They have two supply pins: V+ and GND. V+ and GND are used to drive the internal CMOS switches and set the limits of the analog voltage on any switch. Reverse ESD-protection diodes are internally connected between each analog signal pin and both V+ and GND. If any analog signal exceeds V+ or GND, one of these diodes will conduct. During normal operation, these (and other) reversebiased ESD diodes leak, forming the only current drawn from V+ or GND. Virtually all the analog leakage current comes from the ESD diodes. Although the ESD diodes on a given signal pin are identical, and therefore fairly well balanced, they are reverse-biased differently. Each is biased by either V+ or GND and the analog signal. This means that leakage will vary as the signal varies. The difference in the two diode leakages to the V+ and GND pins constitutes the analog signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of either the same or opposite polarity.

### \_Test Circuits/Timing Diagrams

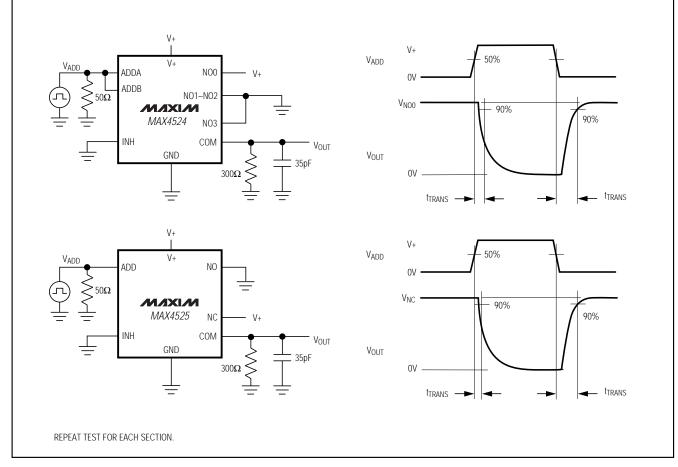


Figure 1. Address Transition Time



**MAX4524/MAX4525** 

There is no connection between the analog signal paths and GND. V+ and GND power the internal logic and logic-level translators, and set both the input and output logic limits. The logic-level translators convert the logic levels into switched V+ and GND signals to drive the gates of the analog signals. This drive signal is the only connection between the logic supplies (and signals) and the analog supplies. V+ has an ESD-protection diode to GND.

#### Low-Voltage Operation

These devices operate from a single supply between +2V and +12V. At room temperature, they actually "work" with a single supply at near or below +1.7V, although as supply voltage decreases, switch on-resistance and switching times become very high.

#### **High-Frequency Performance**

In 50 $\Omega$  systems, signal response is reasonably flat up to 50MHz (see *Typical Operating Characteristics*). Above 20MHz, the on-response has several minor peaks, which are highly layout dependent. The problem is not turning the switch on, but turning it off. The offstate switch acts like a capacitor, and passes higher frequencies with less attenuation. At 10MHz, off-isolation is about -50dB in 50 $\Omega$  systems, becoming worse (approximately 20dB per decade) as frequency increases. Higher circuit impedances also degrade offisolation. Adjacent channel attenuation is about 3dB above that of a bare IC socket, and is entirely due to capacitive coupling.

### Test Circuits/Timing Diagrams (continued)

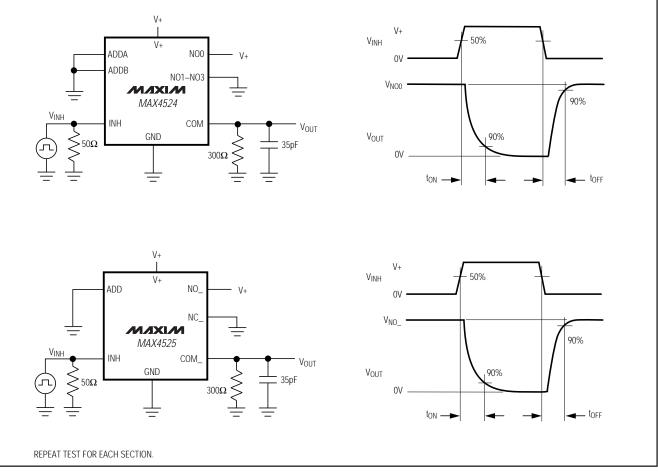


Figure 2. Inhibit Switching Times

Test Circuits/Timing Diagrams (continued)

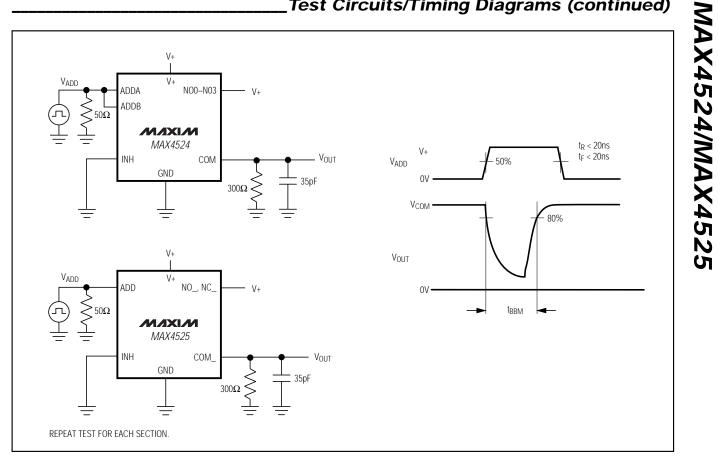


Figure 3. Break-Before-Make Interval

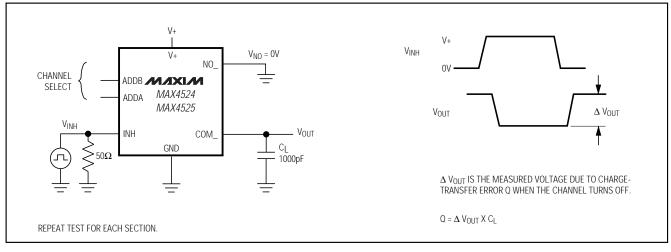


Figure 4. Charge Injection



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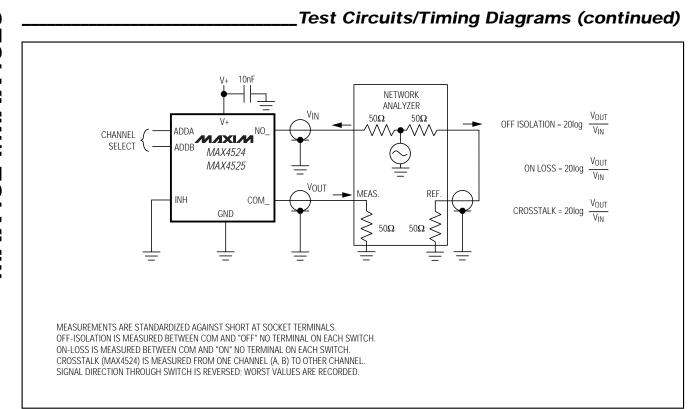


Figure 5. Off-Isolation, On-Loss, and Crosstalk

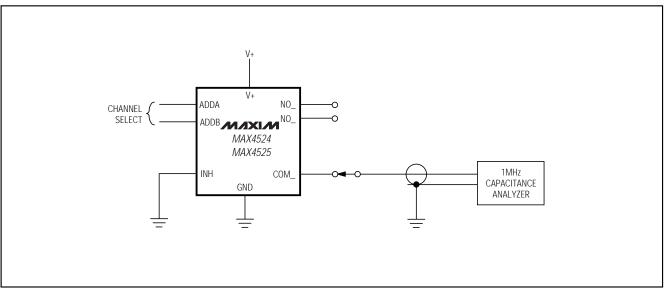
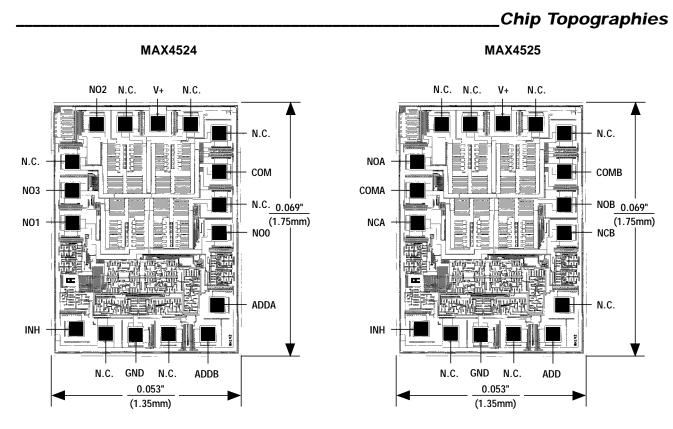
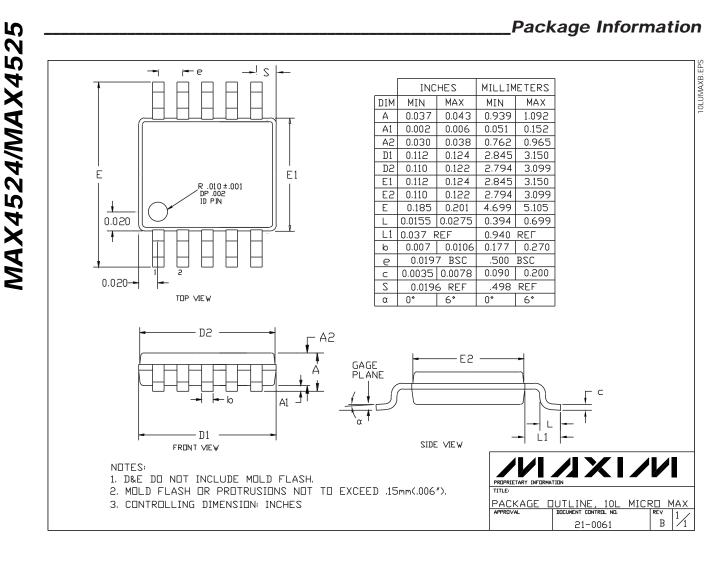


Figure 6. NO/COM Capacitance



N.C. = No Connection

TRANSISTOR COUNT: 219 SUBSTRATE CONNECTED TO V+



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